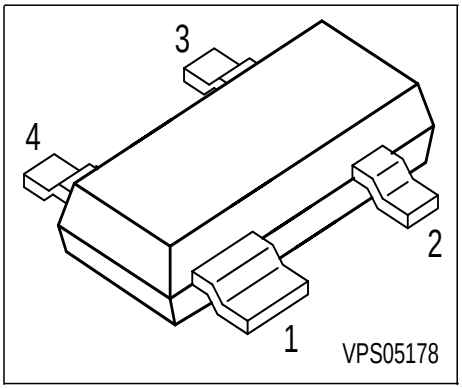
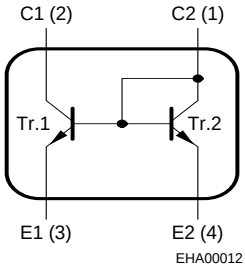
NPN Silicon Double Transistor

- To be used as a current mirror
- Good thermal coupling and V_{BE} matching
- High current gain
- Low collector-emitter saturation voltage





Type	Marking	Pin Configuration				Package
BCV61A	1Js	1 = C2	2 = C1	3 = E1	4 = E2	SOT143
BCV61B	1Ks	1 = C2	2 = C1	3 = E1	4 = E2	SOT143
BCV61C	1Ls	1 = C2	2 = C1	3 = E1	4 = E2	SOT143

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage (transistor T1)	V_{CEO}	30	V
Collector-base voltage (open emitter) (transistor T1)	V_{CBO}	30	
Emitter-base voltage	V_{EBS}	6	
DC collector current	I_C	100	mA
Peak collector current	I_{CM}	200	
Base peak current (transistor T1)	I_{BM}	200	
Total power dissipation, T_S = 99 °C	P_{tot}	300	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Junction - soldering point[1)]	R_{thJS}	≤170	K/W

[1)] For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter		Symbol	Values			Unit
			min.	typ.	max.	
DC Characteristics of T1						
Collector-emitter breakdown voltage I_C = 10 mA, I_B = 0		$V_{(BR)CEO}$	30	-	-	V
Collector-base breakdown voltage I_C = 10 µA, I_B = 0		$V_{(BR)CBO}$	30	-	-	
Emitter-base breakdown voltage I_E = 10 µA, I_C = 0		$V_{(BR)EBO}$	6	-	-	
Collector cutoff current V_{CB} = 30 V, I_E = 0		I_{CBO}	-	-	15	nA
Collector cutoff current V_{CB} = 30 V, I_E = 0 , T_A = 150 °C		I_{CBO}	-	-	5	µA
DC current gain 1) I_C = 0.1 mA, V_{CE} = 5 V		h_{FE}	100	-	-	-
DC current gain 1) I_C = 2 mA, V_{CE} = 5 V		h_{FE}				
	BCV61A		110	180	220	
	BCV61B		200	290	450	
	BCV61C		420	520	800	
Collector-emitter saturation voltage1)		V_{CEsat}				mV
I_C = 10 mA, I_B = 0.5 mA			-	90	250	
I_C = 100 mA, I_B = 5 mA			-	200	600	
Base-emitter saturation voltage 1)		V_{BEsat}				
I_C = 10 mA, I_B = 0.5 mA			-	700	-	
I_C = 100 mA, I_B = 5 mA			-	900	-	
Base-emitter voltage 1)		$V_{BE(ON)}$				
I_C = 2 mA, V_{CE} = 5 V			580	660	700	
I_C = 10 mA, V_{CE} = 5 V			-	-	770	

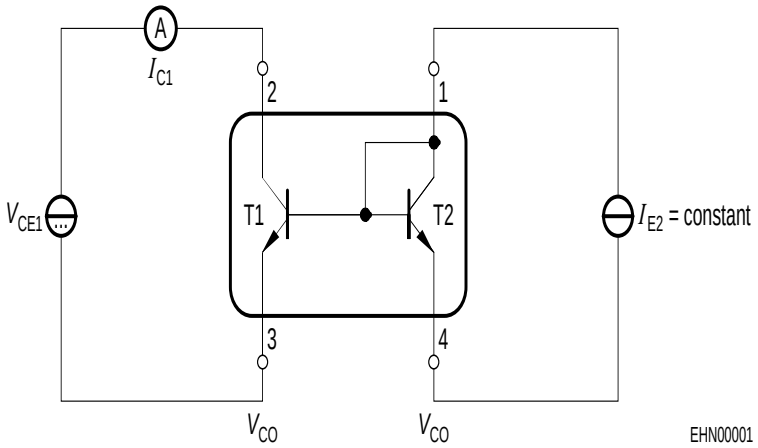
1) Pulse test: t ≤ 300µs, D = 2%

Electrical Characteristics at T_A = 25°C, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Base-emitter forward voltage	V_{BES}				V
I_E = 10 µA		0.4	-	-	
I_E = 250 mA		-	-	1.8	
Matching of transistor T1 and transistor T2	I_{C1} / I_{C2}				-
at I_{E2} = 0.5mA and V_{CE1} = 5V		-	-	-	
T_A = 25 °C		0.7	-	1.3	
T_A = 150 °C		0.7	-	1.3	
Thermal coupling of transistor T1 and transistor T2 [1] T1: V_{CE} = 5V Maximum current of thermal stability of I_{C1}	I_{E2}	-	5	-	mA
AC characteristics for transistor T1					
Transition frequency	f_T	-	250	-	MHz
I_C = 10 mA, V_{CE} = 5 V, f = 100 MHz					
Collector-base capacitance	C_{cb}	-	3	-	pF
V_{CB} = 10 V, f = 1 MHz					
Emitter-base capacitance	C_{eb}	-	8	-	
V_{EB} = 0.5 V, f = 1 MHz					
Noise figure	F	-	2	-	dB
I_C = 200 µA, V_{CE} = 5 V, R_S = 2 kΩ,					
f = 1 kHz, Δ f = 200 Hz					
Short-circuit input impedance	h_{11e}	-	4.5	-	kΩ
I_C = 1 mA, V_{CE} = 10 V, f = 1 kHz					
Open-circuit reverse voltage transf.ratio	h_{12e}	-	2	-	10^{-4}
I_C = 1 mA, V_{CE} = 10 V, f = 1 kHz					
Short-circuit forward current transf.ratio	h_{21e}	100	-	900	-
I_C = 1 mA, V_{CE} = 10 V, f = 1 kHz					
Open-circuit output admittance	h_{22e}	-	30	-	µS
I_C = 1 mA, V_{CE} = 10 V, f = 1 kHz					

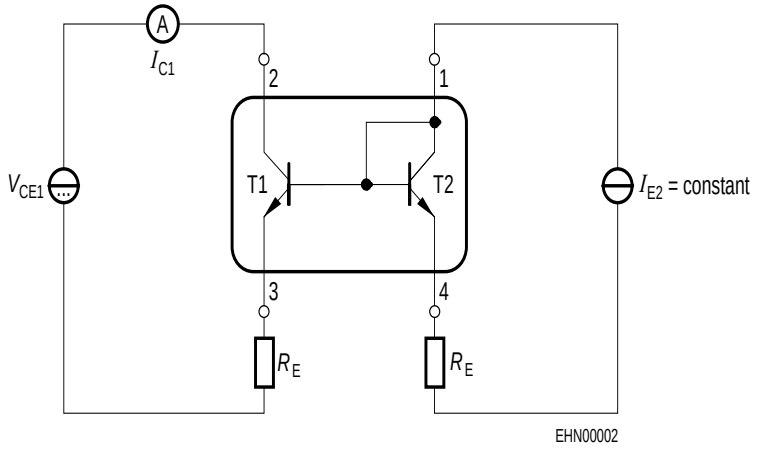
1) Witout emitter resistor. Device mounted on alumina 15mm x 16.5mm x 0.7mm

Test circuit for current matching



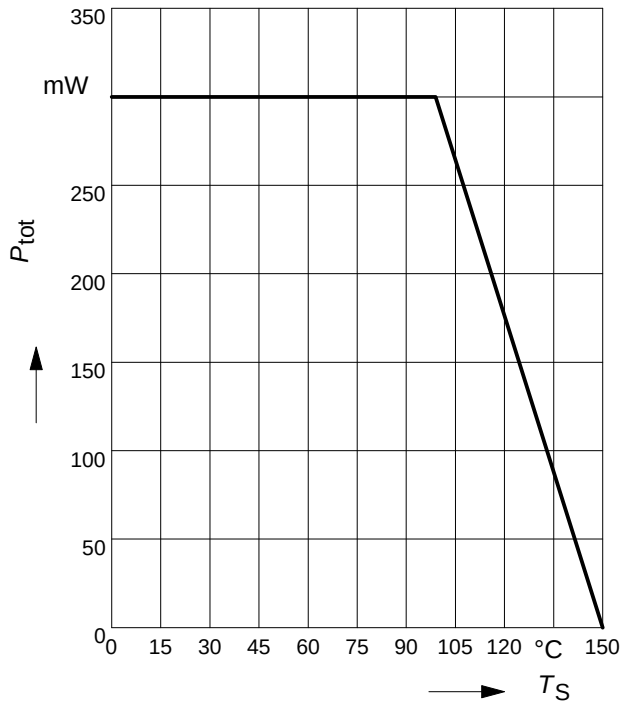
Note: Voltage drop at contacts: $V_{CO} < 2/3\ V_T = 16mV$

Characteristic for determination of V_{CE1} at specified R_E range with I_{E2} as parameter under condition of $I_{C1}/I_{E2} = 1.3$



Note: BCV61 with emitter resistors

Total power dissipation $P_{tot} = f(T_S)$



Permissible pulse load

$P_{totmax} / P_{totDC} = f(t_p)$